



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-11.5 A

Features

- R_{DS(ON)}, V_{GS}@-10V, I_D@-6A<110mΩ
- R_{DS(ON)}, V_{GS}@-4.5V, I_D@-3A<130mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams

DFN5060-8L

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

			I		
PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	- I _D	-11.5		
	T _C =100°C		-7.2	А	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-35		
Power Dissipation	T _C =25°C	Po	26	W	
	T _C =100°C		10		
Continuous Drain Current (Note 4)	T _A =25°C	I _D	-3.2	А	
	T _A =70°C		-2.5		
Power Dissipation	T _A =25°C	Po	2	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	20	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	4.8	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_{D} =-250uA V_{DS} = V_{GS} , I_{D} =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$		-1	-1.7	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10V, I _D =-6A	-	87	110	mΩ
		V_{GS} =-4.5V, I_D =-3A	-	110	130	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V, V _{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V _{DS} =-30V, I _D =-4A, V _{GS} =-10V ^(Note 2,3)	-	10	-	nC
Gate-Source Charge	Q_{gs}		-	1.6	-	
Gate-Drain Charge	Q_{gd}		-	3	-	
Input Capacitance	Ciss	V _{DS} =-30V, V _{GS} =0V, f=1MHZ	-	785	-	pF
Output Capacitance	Coss		-	175	-	
Reverse Transfer Capacitance	Crss		-	112	-	
Turn-On Delay Time	td _(on)	$V_{DS}\text{=-}30\text{V}, \ R_L\text{=}30\Omega, \\ V_{GS}\text{=-}10\text{V}, \ R_G\text{=}6.2\Omega$ (Note 2,3)	-	8	-	
Turn-On Rise Time	t _r		-	15	-	ns
Turn-Off Delay Time	td _(off)		-	43	-	
Turn-Off Fall Time	t _f		-	8.4	-	
Drain-Source Diode						
Maximum Continuous Drain-Source					11.5	
Diode Forward Current	I _S			-	-11.5	Α
Diode Forward Voltage	V_{SD}	I _S =-1A, V _{GS} =0V	-	-0.76	-1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{θJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =-20A, V_{DD} =-25V, V_{GS} =-10V.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

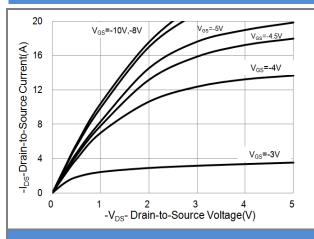


Fig.1 Output Characteristics

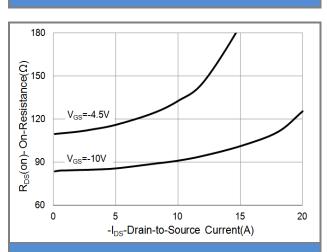
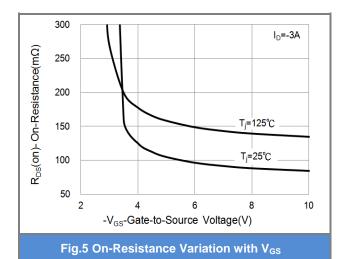


Fig.3 On-Resistance vs. Drain Current



20 V_{DS}=-5V V_D

Fig.2 Transfer Characteristics

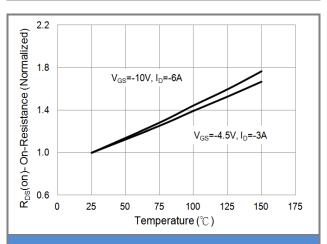


Fig.4 On-Resistance vs. Junction temperature

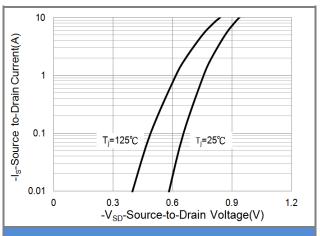


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

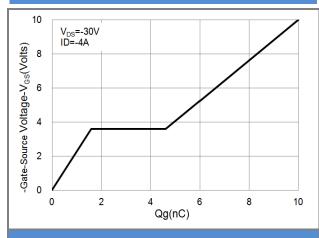


Fig.7 Gate-Charge Characteristics

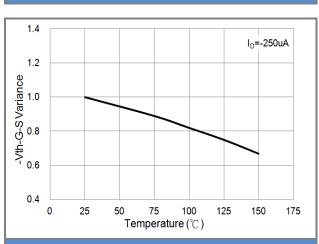
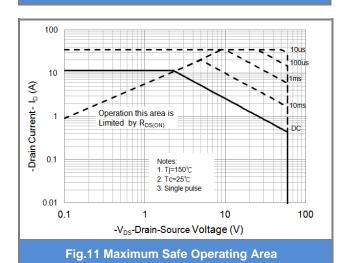


Fig.9 Threshold Voltage Variation with Temperature



TIFICAL CHARACTERISTIC CORVES

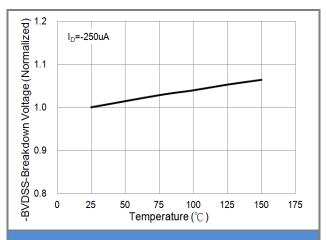


Fig.8 Breakdown Voltage Variation vs. Temperature

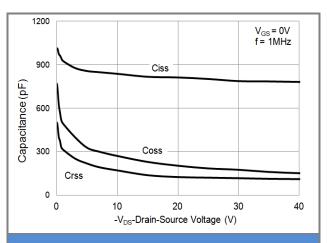


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

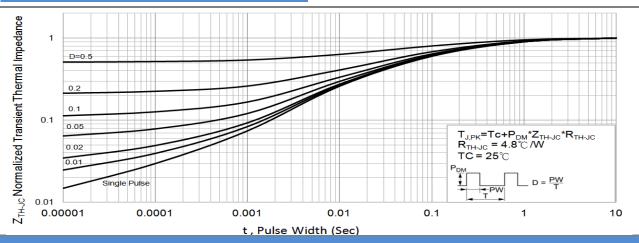


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

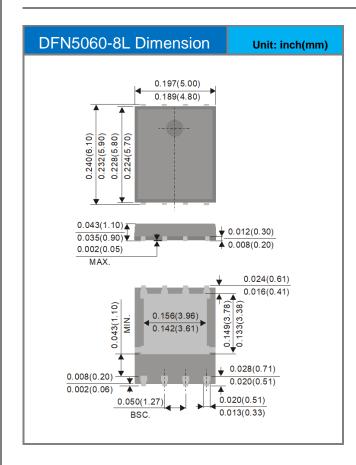


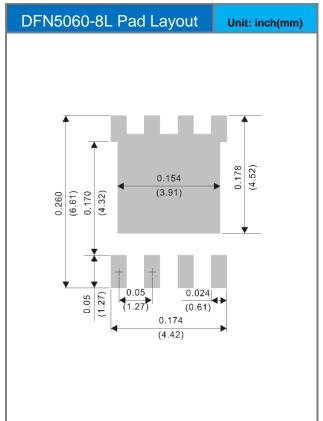


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5461A-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5461A	Halogen free

Packaging Information & Mounting Pad Layout









Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
 responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
 representation or warranty that such applications will be suitable for the specified use without further testing or
 modification.
- The products shown herein are not designed and authorized for equipments relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.

单击下面可查看定价,库存,交付和生命周期等信息

>>Panjit(强茂)